

AMENDMENTS TO THE CLAIMS

1. (Cancelled)
2. (Cancelled)
3. (Cancelled)
4. (Currently Amended) ~~Method~~ The method according to claim 23, ~~characterized in that said wherein the~~ first deposited layer (~~52, 54~~) and said further deposited layer (~~116~~) are metallic.
5. (Currently Amended) ~~Method~~ The method according to claim 4, ~~characterized in that said wherein the~~ first deposited layer (~~52, 54~~) and said further deposited layer (~~116~~) include at least one layer of gold or of titanium or of platinum.
6. (Currently Amended) ~~Method~~ The method according to claim 4, ~~characterized in that said wherein the~~ first deposited layer (~~52, 54~~) and said further deposited layer (~~116~~) include at least one layer of gold/tin alloy.
7. (Currently Amended) ~~Method~~ The method according to claim 23, ~~characterized in that said wherein the further~~ deposited layer (~~116~~) and said first deposited layer (~~52, 54~~) comprise

non metallic materials.

8. (Currently Amended) ~~Method~~ The method according to claim 7, ~~characterized in that~~
~~said~~ wherein the nonmetallic materials comprise an oxide.

9. (Currently Amended) ~~Method~~ The method according to claim 7, ~~characterized in that~~
~~said~~ wherein the nonmetallic materials comprise a carbide.

10. (Currently Amended) ~~Method~~ The method according to claim 7, ~~characterized in~~
~~that said~~ wherein the nonmetallic materials comprise a nitride.

11. (Cancelled)

12. (Cancelled)

13. (Cancelled)

14. (Currently Amended) ~~Method~~ The method according to claim 13, ~~characterized in~~
~~that said~~ 26, wherein the first deposited layer (52, 54) and said further deposited layer (116) are
metallic.

15. (Currently Amended) ~~Method~~ The method according to claim 14, ~~characterized in that said~~ wherein the first deposited layer (52, 54) and said further deposited layer (116) comprise at least one layer of gold or of titanium or of platinum.

16. (Currently Amended) ~~Method~~ The method according to claim 14, ~~characterized in that said~~ wherein the first deposited layer (52, 54) and said further deposited layer (116) comprise at least one layer of gold/tin alloy.

17. (Currently Amended) ~~Method~~ The method according to claim 13, ~~characterized in that said~~ 26, wherein the first deposited layer (52, 54) and said further deposited layer (116) are made of nonmetallic materials.

18. (Currently Amended) ~~Method~~ The method according to claim 17, ~~characterized in that said~~ wherein the nonmetallic materials comprise an oxide.

19. (Currently Amended) ~~Method~~ The method according to claim 17, ~~characterized in that said~~ wherein the nonmetallic materials comprise a carbide.

20. (Currently Amended) ~~Method~~ The method according to claim 17, ~~characterized in that said~~ wherein the nonmetallic materials comprise a nitride.

21. (New) A method for selectively covering a micro machined surface on a die comprising an upper face and at least one etched recess located in the upper face, the method comprising:

applying a film of negative photoresist onto the upper face, the film of negative photoresist covering the at least one etched recess without filling the at least one etched recess;

exposing the film of negative photoresist to ultraviolet radiation through a first mask, the first mask having a window coextensive with at least the at least one etched recess, thereby polymerizing a region of the film of negative photoresist covering the at least one etched recess;

removing a non-polymerized portion of the film of negative photoresist from the upper face, thereby leaving a covering of polymerized film over the at least one etched recess;

applying a layer of lift off resist over the upper face of the die and over the covering; and

applying a layer of positive photoresist over the layer of lift off resist.

22. (New) The method according to claim 21, further comprising:

exposing a portion of the layer of positive photoresist to ultraviolet radiation through a window in a second mask to depolymerize the portion of the layer of positive photoresist; and

removing the depolymerized portion of the layer of positive photoresist, thereby forming at least one cavity.

23. (New) The method according to claim 22, further comprising:

applying a first deposited layer on said upper face of said die;

applying a further deposited layer on an upper surface of the layer of positive photoresist;
removing the layer of positive photoresist and the layer of lift off resist using a solvent
that acts through side edges and sub-etchings of the at least one cavity;
casting aside the further deposited layer; and
removing the film of negative photoresist.

24. (New) A method for selectively covering a micro machined surface on a die
comprising an upper face and at least one etched recess located in the upper face, the method
comprising:

applying a film of negative photoresist onto the upper face, the film of negative
photoresist covering the at least one etched recess without filling the at least one etched recess;
exposing the film of negative photoresist to ultraviolet radiation through a first mask, the
first mask having a window coextensive with at least the at least one etched recess, thereby
polymerizing a region of the film of negative photoresist covering the at least one etched recess;
removing a non-polymerized portion of the film of negative photoresist from the upper
face, thereby leaving a covering of polymerized film over the at least one etched recess; and
applying a layer of positive photoresist over the upper face of the die and over the
covering.

25. (New) The method according to claim 24, further comprising:

exposing a portion of the layer of positive photoresist to ultraviolet radiation through a

window in a second mask to depolymerize the portion of the layer of positive photoresist; and
removing the depolymerized portion of the layer of positive photoresist, thereby forming
at least one cavity.

26. (New) The method according to claim 25, further comprising:
applying a first deposited layer on said upper face of said die;
applying a further deposited layer on an upper surface of the layer of positive photoresist;
removing the layer of positive photoresist using a solvent that acts through walls of the at
least one cavity;
casting aside the further deposited layer; and
removing the film of negative photoresist.